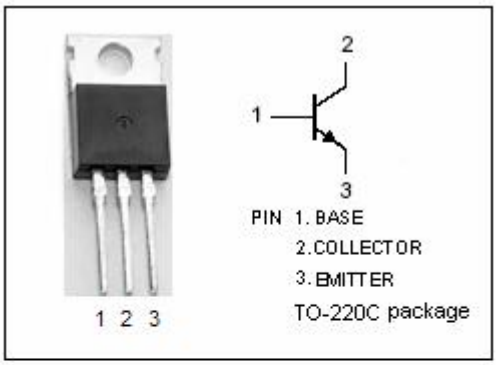
isc Silicon NPN Power Transistor — 2SC3676

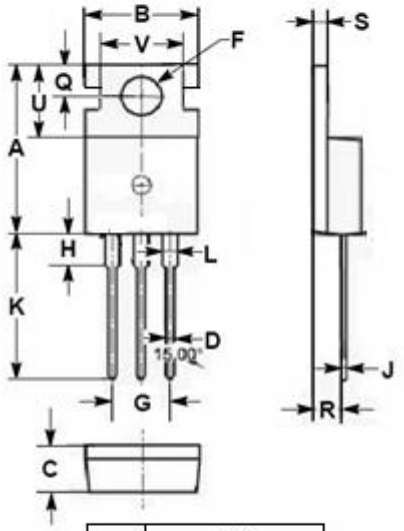
DESCRIPTION

- Low Collector Saturation Voltage
- High breakdown voltage
- Small Cob
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- High voltage amplifier
- High-voltage switching applications
- Dynamis focus applications



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	900	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.3	A
I_{CM}	Collector Current-Pulse	1.0	A
P_C	Collector Power Dissipation @ T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA ; I_B= 0	900			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=60mA; I_B=12mA			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 60mA; I_B= 12mA			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 900V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			10	μA
h_{FE}	DC Current Gain	I_C= 30mA ; V_{CE}= 5V	30			
f_T	Current-Gain—Bandwidth Product	I_E=30mA ; V_{CE}= 10V		6		MHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 100V;f_{test}= 1.0MHz		5.0		pF